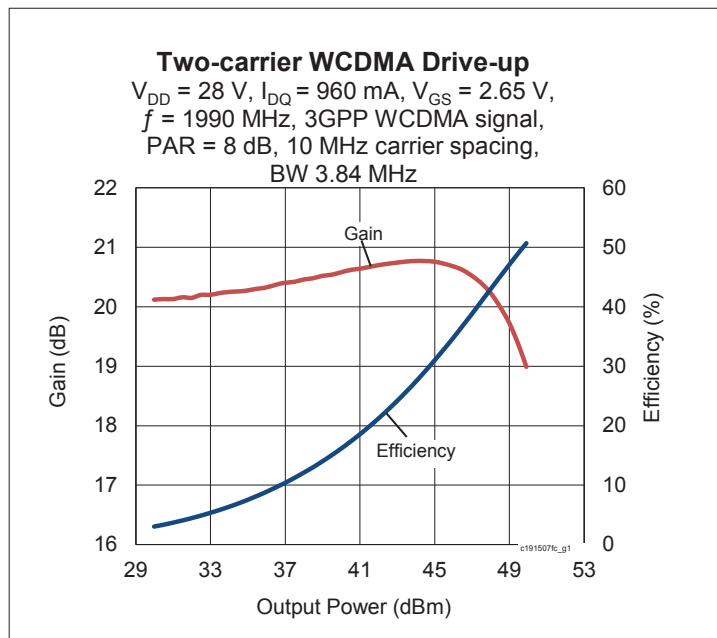
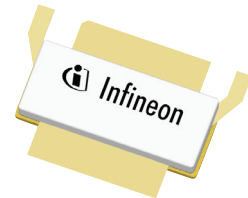


## Thermally-Enhanced High Power RF LDMOS FET 150 W, 28 V, 1805 – 1990 MHz

### Description

The PXFC191507FC is a 150-watt LDMOS FET intended for use in multi-standard cellular power amplifier applications in the 1805 to 1990 MHz frequency band. Features include input and output matching, high gain and thermally-enhanced package with earless flanges. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.

PXFC191507FC  
Package H-37248G-4/2



### Features

- Broadband internal input and output matching
- Typical Pulsed CW performance, 1990 MHz, 28 V, 10  $\mu\text{s}$  pulse width, 10% duty cycle, class AB test
  - Output power at  $P_{1dB} = 140\text{ W}$
  - Efficiency = 54%
  - Gain = 19.5 dB
- Typical single-carrier WCDMA performance, 1990 MHz, 28 V, 10 dB PAR @ 0.01% CCDF, Test Model 1 with 16DPCH
  - Output power = 32 W avg
  - Efficiency = 34%
  - Gain = 20 dB
  - ACPR = -31 dBc @ 5 MHz
- Capable of handling 10:1 VSWR @ 28 V, 150 W (CW) output power
- Integrated ESD protection : Human Body Model, Class 1C (per JESD22-A114)
- Low thermal resistance
- Pb-free and RoHS compliant

### RF Characteristics

#### Two-carrier WCDMA Specifications (tested in Infineon production test fixture)

$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 960\text{ mA}$ ,  $P_{OUT} = 32\text{ W avg}$ ,  $f_1 = 1980\text{ MHz}$ ,  $f_2 = 1990\text{ MHz}$ , 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 8 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	19	20.5	—	dB
Drain Efficiency	$\eta_D$	29	31	—	%
Intermodulation Distortion	IMD	—	-33	-31	dBc

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

**ESD:** Electrostatic discharge sensitive device—observe handling precautions!

**DC Characteristics** (each side)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	0.05	1	$\mu\text{A}$
	$V_{DS} = 63\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	10	$\mu\text{A}$
On-State Resistance	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.05	—	$\Omega$
Operating Gate Voltage	$V_{DS} = 26\text{ V}$ , $I_{DQ} = 960\text{ mA}$	$V_{GS}$	2.3	2.6	2.9	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	—	—	1	$\mu\text{A}$

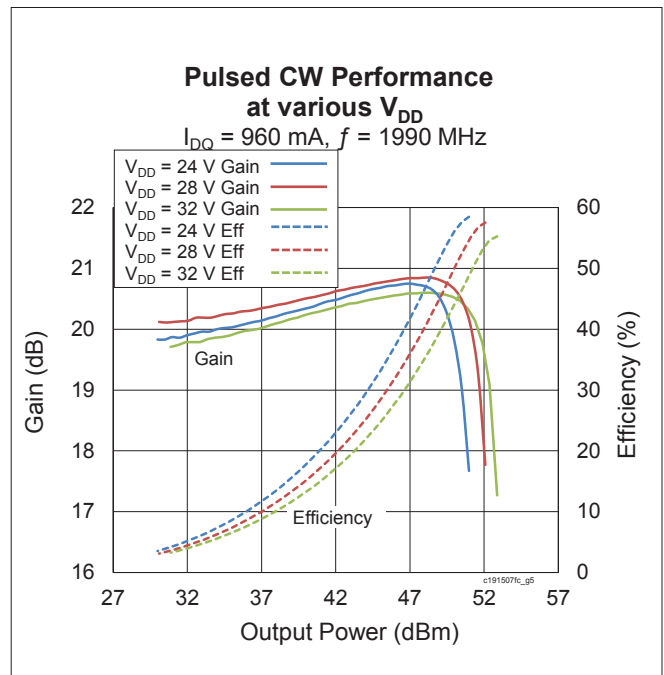
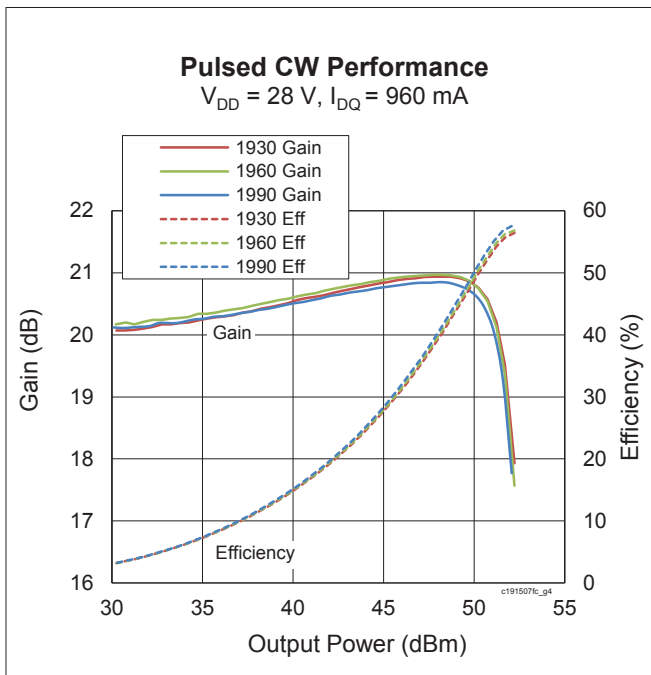
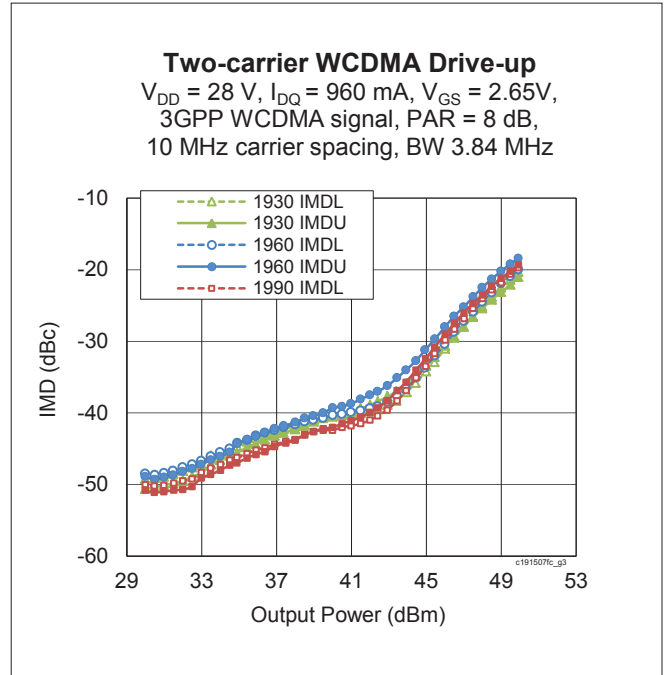
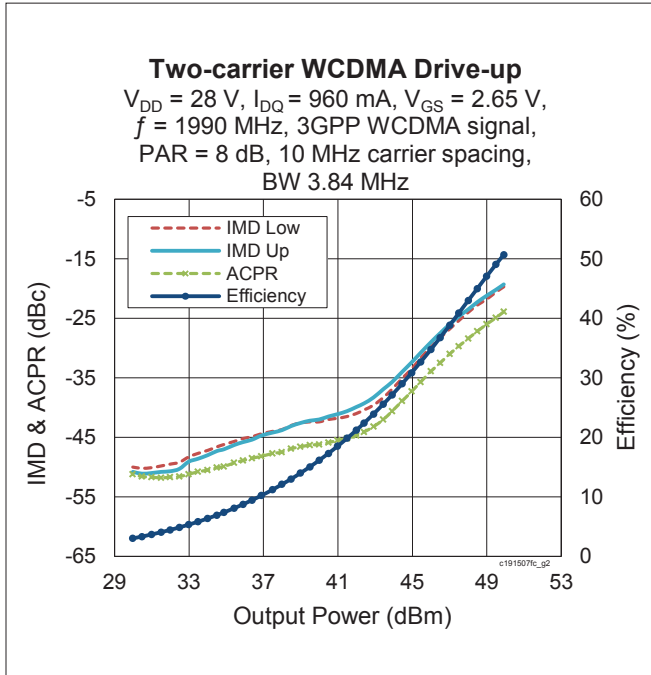
**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	V
Gate-Source Voltage	$V_{GS}$	-6 to +10	V
Operating Voltage	$V_{DD}$	0 to +32	V
Junction Temperature	$T_J$	225	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance ( $T_{CASE} = 70^{\circ}\text{C}$ , 140 W CW)	$R_{\theta JC}$	0.43	$^{\circ}\text{C/W}$

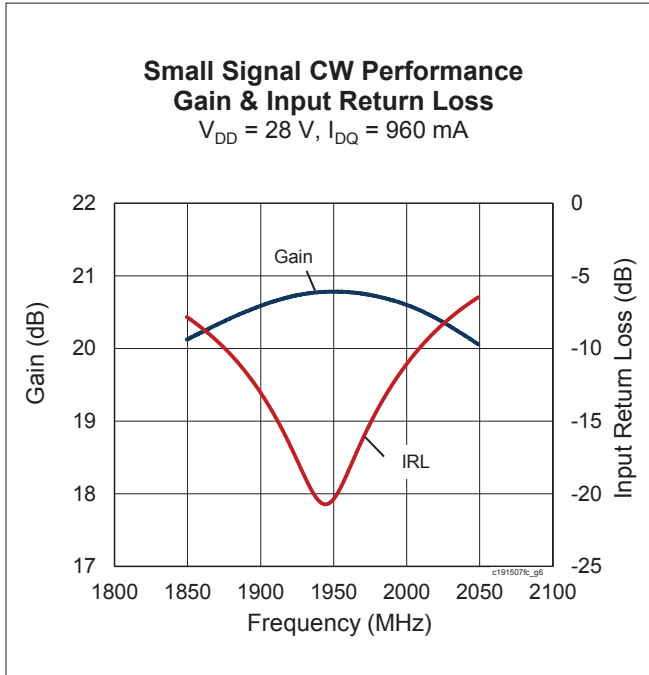
**Ordering Information**

Type and Version	Order Code	Package Description	Shipping
PXFC191507FC V1	PXFC191507FCV1XWSA1	H-37248G-4/2, earless flange	Tray
PXFC191507FC V1 R250	PXFC191507FCV1R250XTMA1	H-37248G-4/2, earless flange	Tape & Reel, 250 pcs

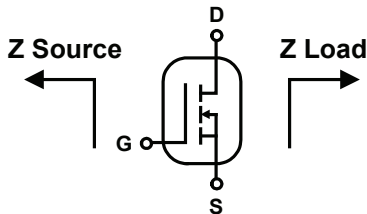
**Typical Performance** (data taken in a production test fixture)



Typical Performance (cont.)



Broadband Circuit Impedance



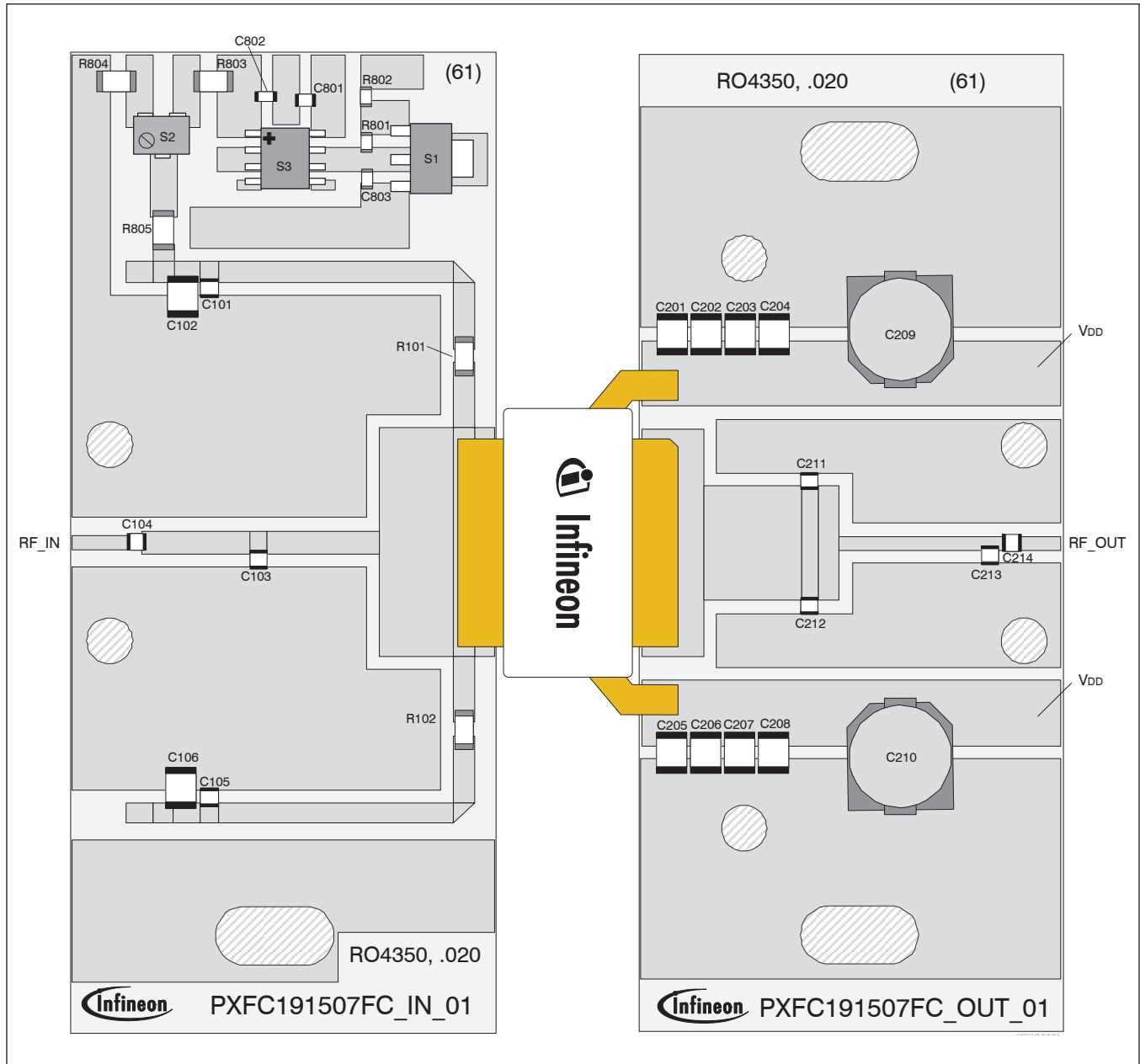
Freq [MHz]	Z Source $\Omega$		Z Load $\Omega$	
	R	jX	R	jX
1930	1.34	-4.30	1.55	-3.14
1960	1.28	-4.15	1.54	-2.99
1990	1.25	-4.04	1.52	-2.86

Load Pull Performance

Main Side Load Pull Performance – Pulsed CW signal: 100  $\mu\text{s}$ , 10% duty cycle,  $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 960\text{ mA}$

Freq [MHz]	Zs [ $\Omega$ ]	P <sub>1dB</sub>									
		Max Output Power					Max PAE				
		ZI [ $\Omega$ ]	Gain [dB]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	PAE [%]	ZI [ $\Omega$ ]	Gain [dB]	P <sub>OUT</sub> [dBm]	P <sub>OUT</sub> [W]	PAE [%]
1805	1.00 - j3.39	1.36 - j2.81	18.2	52.30	170	58.1	2.82 - j2.46	20.4	50.40	110	65.7
1880	1.38 - j3.80	1.26 - j3.35	17.8	52.10	164	54.7	2.48 - j2.33	20.2	50.50	112	64.8
1930	1.88 - j4.65	1.14 - j3.38	17.6	52.10	162	52.1	2.25 - j2.06	20.1	50.20	104	63.7
1990	2.85 - j4.62	1.31 - j3.40	18.4	52.00	157	56.4	1.81 - j2.40	19.9	50.60	116	62.8

Reference Circuit , 1930 – 1990 MHz



Reference circuit assembly diagram (not to scale)

**Reference Circuit** (cont.)

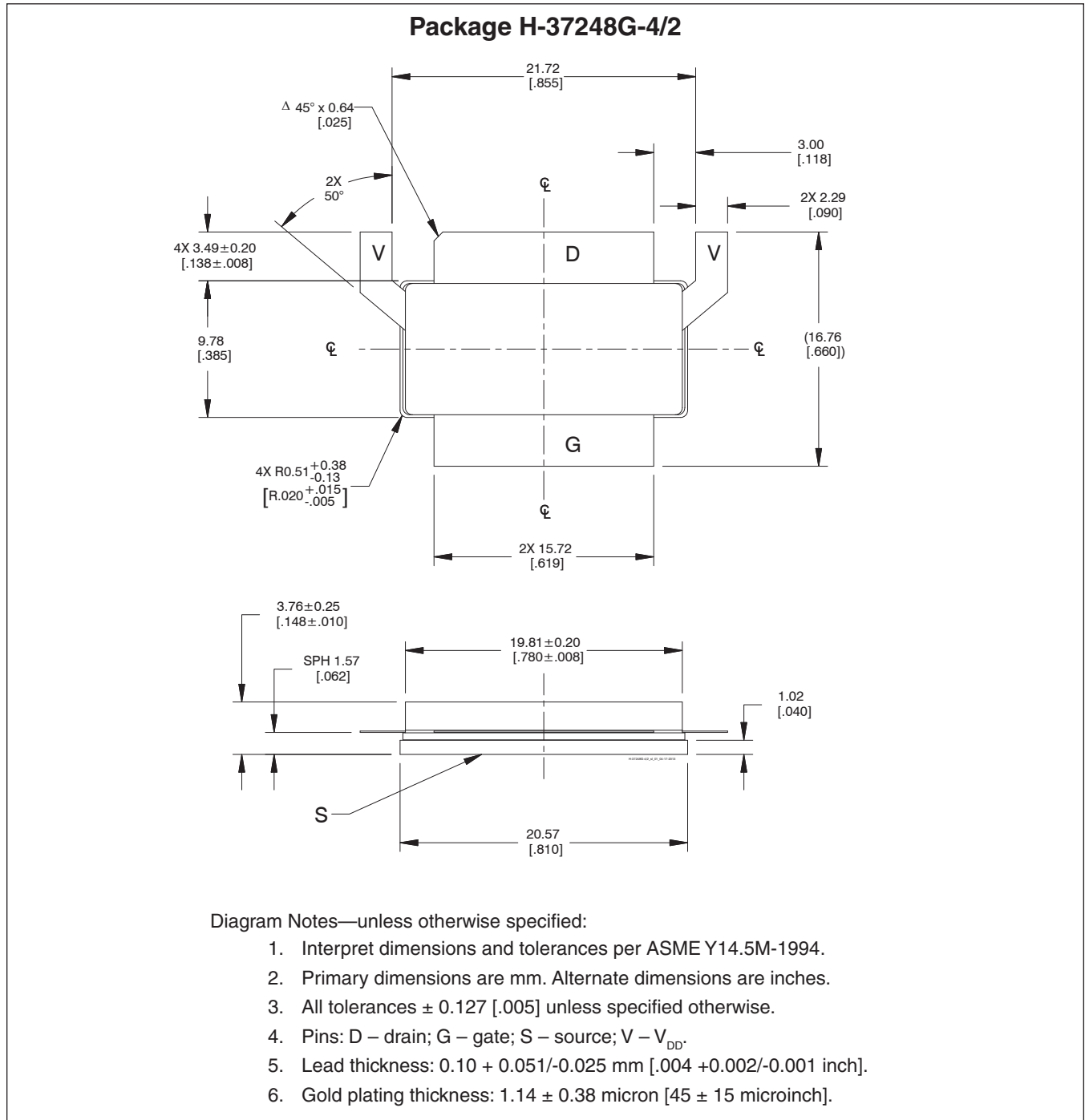
**Reference Circuit Assembly**

DUT	PXFC191507FC V1
Test Fixture Part No.	LTN/PXFC191507FC V1
PCB	Rogers 4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\epsilon_r = 3.66$ , $f = 1930 - 1990$ MHz
Find Gerber files for this test fixture on the Infineon Web site at <a href="http://www.infineon.com/rfpower">http://www.infineon.com/rfpower</a>	

**Components Information**

Component	Description	Suggested Manufacturer	P/N
<b>Input</b>			
C101, C104, C105,	Capacitor, 33 pF	ATC	ATC800A330JT250
C102, C106	Capacitor, 10 $\mu$ F	Taiyo Yuden	UMK325C7106MM-T
C103	Capacitor, 1.0 pF	ATC	ATC800A1R0BT250
C801, C802, C803	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
R101, R102, R805	Capacitor, 10 ohms	Panasonic Electronic Components	ERJ-8GEYJ100V
R801	Resistor, 1200 Ohm	Panasonic Electronic Components	ERJ-3GEYJ122V
R802	Resistor, 1300 Ohm	Panasonic Electronic Components	ERJ-3GEYJ132V
R803, R804	Capacitor, 100 ohms	Panasonic Electronic Components	ERJ-8GEYJ101V
S1	Transistor	Infineon Technologies	BCP56
S2	Potentiometer, 2k $\Omega$	Bourns Inc.	3224W-1-202E
S3	Voltage Regulator	Texas Instruments	LM7805
<b>Output</b>			
C201, C202, C203, C204, C205, C206, C207, C208	Capacitor, 10 $\mu$ F	Taiyo Yuden	UMK325C7106MM-T
C209, C210	Capacitor, 220 $\mu$ F	Panasonic Electronic Components	EEE-FP1V221AP
C211, C212, C213	Capacitor, 0.3 pF	ATC	ATC800A0R3BT250
C214	Capacitor, 33 pF	ATC	ATC800A330JT250

## Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page  
<http://www.infineon.com/rfpower>